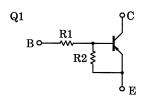
TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process) Silicon NPN Epitaxial Type (PCT Process)

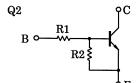
RN4609

Switching, Inverter Circuit, Interface Circuit And Driver Circuit Applications

- Including two devices in SM6 (super mini type with 6 leads)
- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process

Equivalent Circuit and Bias Resister Values





R1: 47kΩ R2: 22kΩ (Q1, Q2 Common)

Q1 Absolute Maximum Ratings (Ta = 25°C)

| Characteristic | Symbol | Rating | Unit |
|---------------------------|------------------|--------|------|
| Collector-base voltage | V_{CBO} | -50 | V |
| Collector-emitter voltage | V _{CEO} | -50 | V |
| Emitter-base voltage | V _{EBO} | -15 | V |
| Collector current | IC | -100 | mA |

Unit in mm 2.8-0.2 2.8-0.3 1.6-0.1 1.6-0.1 2.0 + 6.1 2.0 + 6.1 2.0 + 6.1 3. COLLECTOR 2 (C2) 4. EMITTER 2 (E2) 4. EMITTER 2 (E2) 5. BASE 2 (B2) 6. COLLECTOR 1 (C1) JEDEC EIAJ TOSHIBA 2-3N1A

Weight: 0.015g

Q2 Absolute Maximum Ratings (Ta = 25°C)

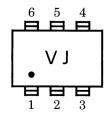
| Characteristic | Symbol | Rating | Unit |
|---------------------------|------------------|--------|------|
| Collector-base voltage | V _{CBO} | 50 | V |
| Collector-emitter voltage | V _{CEO} | 50 | V |
| Emitter-base voltage | V _{EBO} | 15 | V |
| Collector current | IC | 100 | mA |

| Characteristic | Symbol | Rating | Unit |
|-----------------------------|------------------|---------|------|
| Collector power dissipation | P _C * | 300 | mW |
| Junction temperature | Tj | 150 | °C |
| Storage temperature range | T _{stg} | -55~150 | °C |

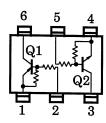
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Marking



Equivalent Circuit (Top View)



^{*} Total rating

Q1 Electrical Characteristics (Ta = 25°C)

| Characteristic | Symbol | Test Circuit | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------------|-----------------------|-----------------|---|--------|------|--------|------|
| Collector cut-off current | I _{CBO} | _ | V _{CB} = −50V, I _E = 0 | _ | _ | -100 | nA |
| | I _{CEO} | _ | $V_{CE} = -50V, I_B = 0$ | _ | _ | -500 | |
| Emitter cut-off current | I _{EBO} | _ | $V_{EB} = -15V$, $I_C = 0$ | -0.167 | _ | -0.311 | mA |
| DC current gain | h _{FE} | _ | $V_{CE} = -5V, I_{C} = -10mA$ | 70 | _ | _ | _ |
| Collector-emitter saturation voltage | V _{CE} (sat) | _ | $I_C = -5\text{mA}, I_B = -0.25\text{mA}$ | _ | -0.1 | -0.3 | V |
| Input voltage (ON) | V _{I (ON)} | _ | $V_{CE} = -0.2V$, $I_{C} = -5mA$ | -2.2 | _ | -5.8 | V |
| Input voltage (OFF) | V _{I (OFF)} | _ | $V_{CE} = -5V, I_{C} = -0.1 \text{mA}$ | -1.5 | _ | -2.6 | V |
| Transition frequency | f _T | _ | V _{CE} = −10V, I _C = −5mA | _ | 200 | _ | MHz |
| Collector output capacitance | C _{ob} | _ | V _{CB} = −10V, I _E = 0 | _ | 3 | 6 | pF |

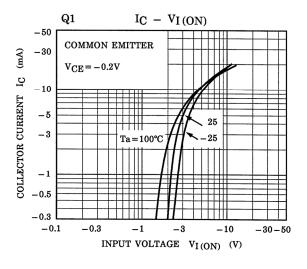
Q2 Electrical Characteristics (Ta = 25°C)

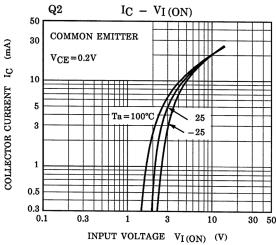
| Characteristic | Symbol | Test Circuit | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------------|-----------------------|-----------------|--|-------|------|-------|------|
| Collector cut-off current | I _{CBO} | _ | V _{CB} = 50V, I _E = 0 | _ | _ | 100 | nA |
| | I _{CEO} | _ | V _{CE} = 50V, I _B = 0 | _ | ١ | 500 | |
| Emitter cut-off current | I _{EBO} | _ | V _{EB} = 15V, I _C = 0 | 0.167 | 1 | 0.311 | mA |
| DC current gain | h _{FE} | _ | V _{CE} = 5V, I _C = 10mA | 70 | _ | _ | _ |
| Collector-emitter saturation voltage | V _{CE} (sat) | _ | I _C = 5mA, I _B = 0.25mA | _ | 0.1 | 0.3 | V |
| Input voltage (ON) | V _{I (ON)} | _ | V _{CE} = 0.2V, I _C = 5mA | 2.2 | _ | 5.8 | V |
| Input voltage (OFF) | V _{I (OFF)} | _ | $V_{CE} = 5V, I_{C} = 0.1mA$ | 1.5 | _ | 2.6 | V |
| Transition frequency | f _T | _ | V _{CE} = 10V, I _C = 5mA | _ | 250 | _ | MHz |
| Collector output capacitance | C _{ob} | _ | V _{CB} = 10V, I _E = 0, f = 1 MHz | _ | 3 | 6 | pF |

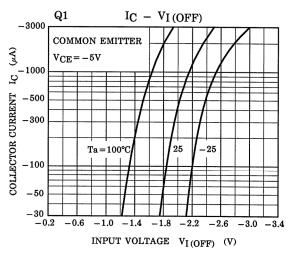
Q1, Q2 Common Electrical Characteristics (Ta = 25°C)

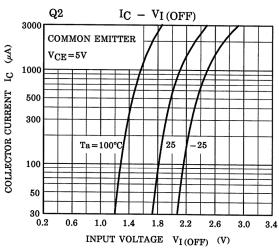
| Characteristic | Symbol | Test Circuit | Test Condition | Min | Тур. | Max | Unit |
|----------------|--------|-----------------|----------------|------|------|------|------|
| Input resistor | R1 | _ | _ | 32.9 | 47 | 61.1 | kΩ |
| Resistor ratio | R1/R2 | _ | _ | 1.92 | 2.14 | 2.35 | _ |

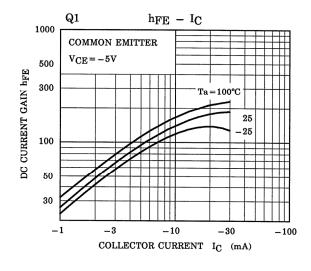
3

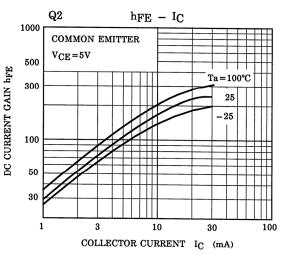












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20070701-EN GENERAL

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